

M82200-9/UM PECVD



Overview

M82200-9/UM PECVD utilizes direct plasma deposition process to grow high quality anti-reflection coating on the surface of solar cell. It is one of the tube film coating devices with the largest per stack capacity.

Benefits



Excellent film uniformity: within wafer $\leq \pm 3\%$, wafer to wafer $\leq \pm 3\%$ and run torun $\leq \pm 2\%$.



300-600°C temperature control range to meet the process requirements of film coating and wafer annealing.



420mm quartz tube to achieve 1800 pcs/h throughput (4 stacks, 308 pcs/stack/run).



 N_2O (laughing gas) pipeline and operation software reserved for anti-PID process.



Full-automatic loading and unloading system, onekey process control and complete alarm and protection function.

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Specification

Process Performance	Film uniformity: within wafer $\leq \pm 3\%$, wafer to wafer $\leq \pm 3\%$, run to run $\leq \pm 2\%$		
	Refractive index uniformity: ≤ ± 0.02		
Throughput	308 pcs/stack, ≥ 1800 pcs/h (4-stack)		
Temperature Control	Flat temperature zone: 1370 mm		
	Method: 5-section cascade control with internal and external thermocouples		
	Range: 300 – 600 °C		
	Precision: ≤ ± 2 ° C/1250 mm		
	Stability: ≤ ± 2 °C/4 h (at 450 °C)		
Pressure Control	Range: 1600 mTorr, ± 300 mTorr adjustable		
	Ultimate vacuum: ≤ 1 Pa		
	Air leakage rate: ≤ 1 Pa/min after pump stopped and valve closed		
	Vacuum recovery speed: AP → 30 mTorr ≤ 2 min		
Boat Conveyor	Double SiC stainless steel or cantilever bar boat conveyor, with continuously adjustable transfer speed of 0 – 3500 mm/min		
	Positioning precision: ≤ ± 0.5 mm		
	Max load: ≥ 25 kg		
Gas Piping System	4 pipelines with MFC control, precision $\leq \pm 1\%$ F.S, leakage rate $\leq 10-7$ Pa.m ³ /s		
Interlock	Furnace door conditions; air pressure, N_2 pressure, water flow pressure and process; special gas valves		
System Dimension	10070 mm \times 1960 mm \times 3070 mm (L \times W \times H, including vacuum pump)		
Power	Peak power: \leq 280 KVA, heat preservation: \leq 100KVA (4-stack)		
Uptime	≥ 97%		
Control Method	Automatic process control and real-time process parameter and procedure monitoring, with fault diagnosis, alarm and protection functions.		
Alarm and Safety	Voice and light indicator for process status; alarm for computer fault and over-temperature; alarm and protection for under-temperature, MFC deviation, reaction chamber pressure deviation and ultimate temperature		

Configuration

Vacuum Pump	Alcatel ADS602H Edwards	ALC ATEL 阿尔卡特 EDWARDS
RF Power	AE PE2-10KW TRUMPF	Advanced Energy.
Temperature Controller	Azbil	azbil

Mass flow meter	HORIBA	HORIBA Scientific
Diaphragm Gauge	INFINCON	INFICON
Industrial PC	Advantech	AD\ANTECH 研華科技
PLC	Mitsubishi	MITSUBISHI ELECTRIC Changes for the Better